

Abstract

A semiconductor substrate, method and device are provided. The substrate is capable of securing a more stable substrate potential and that has a highly reliable SOI structure. A P-type single-crystal silicon layer for forming a device is provided on an insulating layer. In addition, under the insulating layer a P-type support substrate is formed, for example. This support substrate is provided in advance with N-type well patterns. These are deposited as multi-layers so as to comprise a semiconductor substrate having an SOI structure. A predetermined electric potential is applied to each of the well patterns via a connection member that passes through the insulating layer. For example, since a pad is provided in the peripheral region of a chip, regions provided with the well patterns are made to correspond to the pad. Other regions are also provided in accordance with device regions.